

Supplementary Information

Study on the effect of Sn concentration on the structural, optical and electrical properties of $(\text{Al}_{0.55}\text{In}_{0.45})_2\text{O}_3:\text{Sn}$ films

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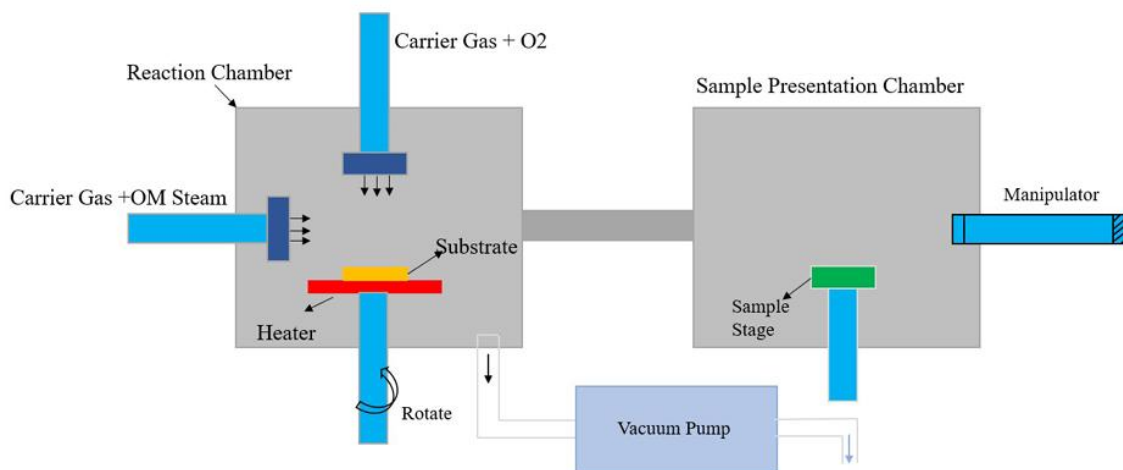


Fig. S1 The graphical representation of the apparatus used for MOVPE deposition in this work

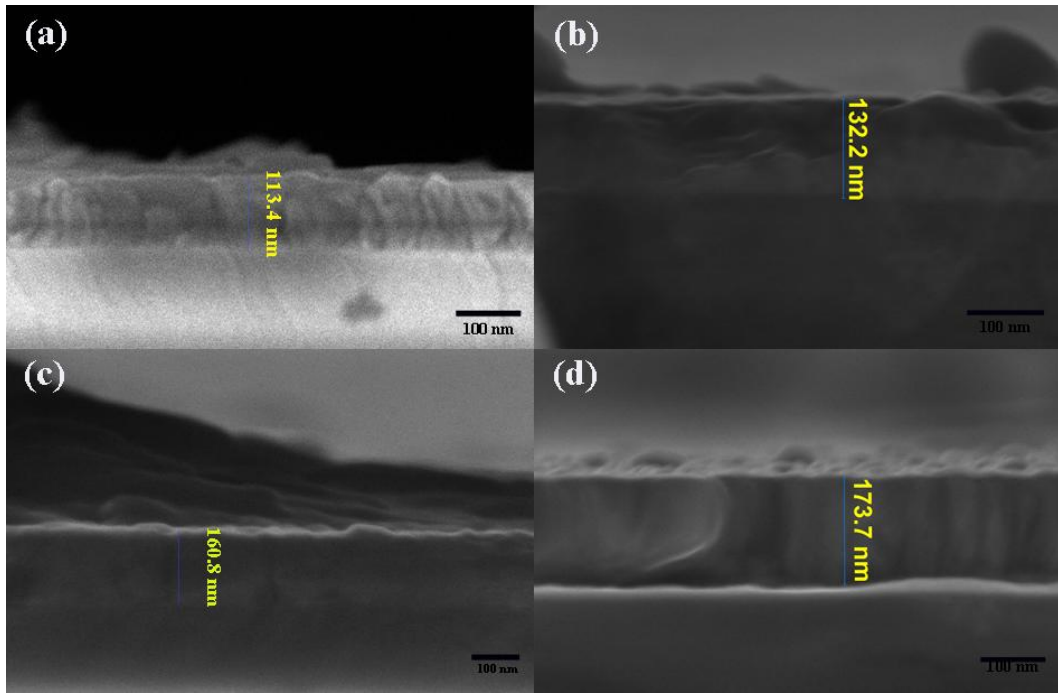


Fig. S2 Cross-sectional SEM images of $(\text{Al}_{0.55}\text{In}_{0.45})_2\text{O}_3:\text{Sn}$ films with different Sn contents: (a) 0, (b) 12%, (c) 21%, (d) 24%